Taiwan Semiconductor

## 0.8A, 200V - 1000V Standard Bridge Rectifier

#### FEATURES

TAIWAN

• AEC-Q101 qualified available

SEMICONDUCTOR

- Ideal for automated placement
- Reliable low cost construction utilizing molded plastic technique
- High surge current capability
- UL Recognized File # E-326854
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application

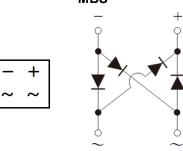
#### **MECHANICAL DATA**

- Case: TO-269AA (MBS)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.120g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I <sub>F</sub>	0.8	А	
V <sub>RRM</sub>	200 - 1000	V	
I <sub>FSM</sub>	35	А	
T <sub>J MAX</sub>	150	°C	
Package	TO-269AA (MBS)		
Configuration	Quad		







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	MBS2	MBS4	MBS6	MBS8	MBS10	UNIT
Marking code on th	e device		MBS2	MBS4	MBS6	MBS8	MBS10	
Repetitive peak rev	erse voltage	$V_{RRM}$	200	400	600	800	1000	V
Reverse voltage, total rms value		V <sub>R(RMS)</sub>	140	280	420	560	700	V
Forward current On glass-epoxy On aluminum substrate		0.5					А	
		I <sub>F</sub>	0.8				А	
Surge peak forward current, 8.3ms single half sine-wave superimposed on rated load		I <sub>FSM</sub>	35					A
Rating for fusing (t<8.3ms)		l <sup>2</sup> t	5.08				A <sup>2</sup> s	
Junction temperature		TJ	- 55 to +150			°C		
Storage temperature		T <sub>STG</sub>	- 55 to +150				°C	





THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-lead thermal resistance <sup>(1)</sup>	R <sub>θJL</sub>	20	°C/W	
Junction-to-ambient thermal resistance <sup>(2)</sup>	R <sub>ØJA</sub>	70	°C/W	
Junction-to-ambient thermal resistance <sup>(1)</sup>	R <sub>ØJA</sub>	85	°C/W	

Notes:

- 1. On glass epoxy P.C.B. mounted on 0.05" x 0.05" (1.3mm x 1.3mm) pads
- On aluminum substrate P.C.B. with an area of 0.8" x 0.8" (20mm x 20mm) mounted on 0.05" x 0.05" (1.3mm x 1.3mm) solder pads

ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER	CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward voltage per diode <sup>(1)</sup>	$I_F = 0.4A, T_J = 25^{\circ}C$	V <sub>F</sub>	-	1	V
$\mathbf{D}$ and $\mathbf{D}$ is tracked by the product of $\mathbf{C}^{(2)}$	$T_J = 25^{\circ}C$	1	-	5	μA
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	T <sub>J</sub> = 125°C	I <sub>R</sub>	-	100	μA
Junction capacitance per diode	$1 MHz, V_R = 4.0 V$	CJ	13	-	pF

#### Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION				
ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING		
MBSx	TO-269AA (MBS)	3,000 / Tape & Reel		
MBSxH	TO-269AA (MBS)	3,000 / Tape & Reel		

#### Notes:

- 1. "x" defines voltage from 200V(MBS2) to 1000V(MBS10)
- 2. "H" means AEC-Q101 qualified



100

10

1

0.1

0.01

10 20 30

40

INSTANTANEOUS REVERSE CURRENT (µA)

#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

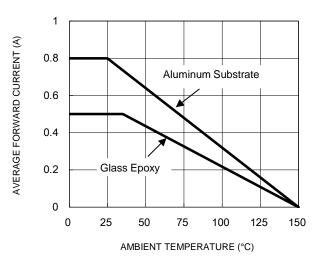
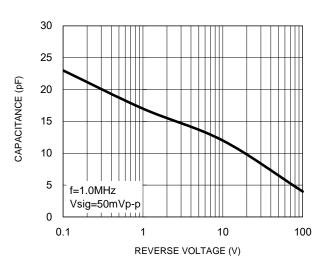


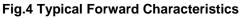
Fig.1 Forward Current Derating Curve

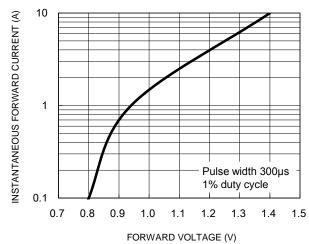
Fig.3 Typical Reverse Characteristics

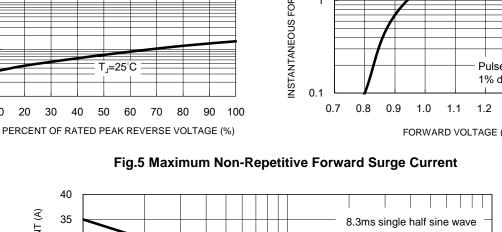
T\_=125°C

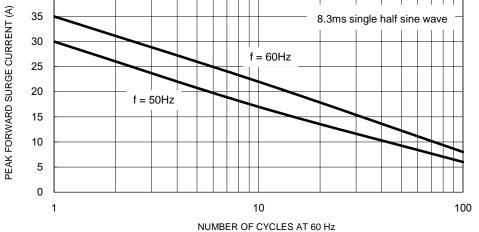


**Fig.2 Typical Junction Capacitance** 



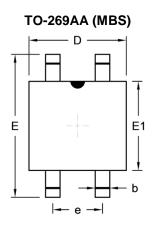


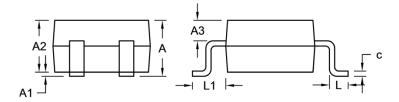






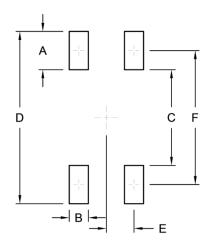
### **PACKAGE OUTLINE DIMENSIONS**





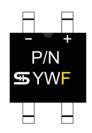
DIM.	Unit (mm)		Unit	(inch)	
	Min.	Max.	Min.	Max.	
A	-	2.90	-	0.114	
A1	-	0.20	-	0.008	
A2	2.30	2.70	0.091	0.106	
A3	0.95	1.53	0.037	0.060	
b	0.56	0.84	0.022	0.033	
с	0.15	0.35	0.006	0.014	
D	4.50	4.90	0.177	0.193	
E	-	6.90	-	0.272	
E1	3.60	5.00	0.142	0.197	
е	2.20	2.60	0.087	0.102	
L	0.70	1.10	0.028	0.043	
L1	1.10	2.12	0.043	0.083	

### SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	1.80	0.071
В	0.90	0.035
С	4.50	0.177
D	8.10	0.319
E	1.30	0.051
F	6.30	0.248

#### **MARKING DIAGRAM**



P/N = M	arking Code
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- = Date Code YW
- F = Factory Code



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